

MICRO ELECTRONICS

2N5225

NPN
SILICON
TRANSISTOR

DESCRIPTION

2N5225 is NPN silicon planar transistor use in general purpose consumer and industrial amplifier and switching applications.

CASE TO-92A



EBC

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	V_{CBO}	25V
Collector-Emitter Voltage	V_{CEO}	25V
Emitter-Base Voltage	V_{EBO}	4V
Collector Current	I_C	200mA
Continuous Power Dissipation	P_d	350mW
Operating & Storage Junction Temperature	T_j, T_{stg}	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS

($T_a = 25^\circ C$)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS	
Collector-Emitter Breakdown Voltage	LV_{CEO}^*	25		V	$I_C = 10mA$	$I_B = 0$
Collector-Base Breakdown Voltage	BV_{CBO}	25			$I_C = 0.1mA$	$I_E = 0$
Collector Cutoff Current	I_{CBO}		300	nA	$V_{CB} = 15V$	$I_E = 0$
Emitter Cutoff Current	I_{EBO}		500	nA	$V_{EB} = 4V$	$I_C = 0$
D.C. Current Gain	H_{FE}^*	25			$I_C = 10mA$	$V_{CE} = 10V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}^*$		0.8	V	$I_C = 100mA$	$I_B = 10mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}^*$		1.1	V	$I_C = 50mA$	$I_B = 2.5mA$
Output Capacitance	C_{ob}		20	pF	$V_{CB} = 10V$	$f = 1MHz$
Current Gain-Bandwidth Product	f_T	50		pF	$I_C = 20mA$	$V_{CE} = 10V$

* Pulse test : pulse width $< 300\mu S$, duty cycle $< 2\%$.



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